

DMN100

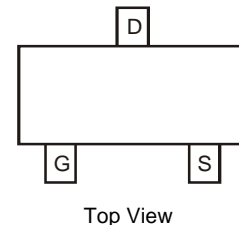
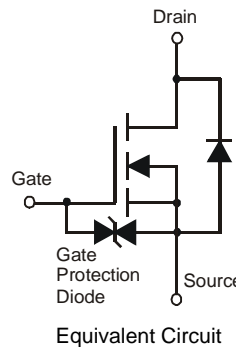
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Extremely Low On-Resistance: 170mΩ @ V_{GS} = 4.5V
- High Drain Current: 1.1A
- Ideal for Notebook Computer, Portable Phone, PCMCIA Cards, and Battery Powered Circuits
- **ESD Protected Gate**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SC59
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.014 grams (approximate)

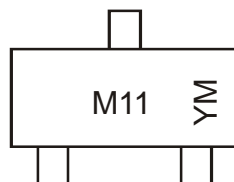


Ordering Information (Note 3)

Part Number	Case	Packaging
DMN100-7-F	SC59	3000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

Marking Information



M11 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: T = 2006)
 M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	T	U	V	W	X	Y	Z	A	B	C	D	E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current	I _D	Continuous	1.1
		Pulsed	4.0

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	P _D	500	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	250	K/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 10	μA	@ T _J = 25°C @ T _J = 125°C V _{DS} = 24V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	± 100	nA	V _{GS} = ± 12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	V _{DS} = 10V, I _D = 1.0mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	0.170 0.150	Ω	V _{GS} = 4.5V, I _D = 0.5A V _{GS} = 10V, I _D = 1.0A
Forward Transconductance	g _{FS}	1.3	2.4	—	S	V _{DS} = 10V, I _D = 0.5A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	150	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	90	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	30	—	pF	
Total Gate Charge	Q _g	—	5.5	—	nC	V _{DS} = 24V, I _D = 1.0A, V _{GS} = 10V
Gate-to-Source Charge	Q _{gs}	—	0.8	—	nC	
Gate-to-Drain Charge	Q _{gd}	—	1.3	—	nC	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = 10V, I _D = 0.5A, V _{GS} = 5.0V, R _{GEN} = 50Ω
Turn-Off Delay Time	t _{D(OFF)}	—	25	—	ns	
Turn-On Rise Time	t _r	—	15	—	ns	
Turn-Off Fall Time	t _f	—	45	—	ns	
SOURCE-DRAIN RATINGS (BODY DIODE)						
Continuous Source Current	I _S	—	—	0.54	A	—
Pulse Source Current	I _{SM}	—	—	4.0	A	—
Forward Voltage	V _{SD}	—	—	1.2	V	I _F = 1.0A, V _{GS} = 0V
Reverse Recovery Time	t _{rr}	—	35	—	ns	I _F = 1.0A, di/dt = 50A/μs

Notes: 2. Pulse width ≤ 300μs, duty cycle ≤ 2%.